

*“InAs<sub>0.85</sub>Sb<sub>0.15</sub> infrared photodiodes grown on GaAs and GaAs-coated Si by molecular beam epitaxy”*. Dobbelaere W, de Boeck J, Heremans P, Mertens R, Borghs G, Luyten W, van Landuyt J, Applied physics letters **600**, 3256 (1992). <http://doi.org/10.1063/1.106711>